



SHEET 1 OF 2

FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-022CPC1

APPLICANT(S): Wu et al.

SERIAL NO.: 10/603,852

FILING DATE: June 25, 2003

GROUP: 2811

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DKO	A249	2002/140031 A1	10/03/2002	Rim			
	A250	2003/003679 A	01/02/2003	Doyle et al.			
	A251	5,013,681	05/07/1991	Godbey et al.			
	A252	5,548,128	08/20/1996	Soref et al.			
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DKO	B53	02-098158	04/10/1990	JP				Y	Y
DKO	B54	06-196673	07/15/1994	JP				Y	Y

EXAMINER

Douglas W. Owens

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OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
<i>OK</i>	C146	Canaperi et al., "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with sustained epitaxial films", IBM, USA (2002) (abstract).	
	C147	Decision of Rejection for Japanese Patent Application Serial No. 2000-544004, August 20, 2002, 2 pages.	
<i>OK</i>	C148	Godbey et al., (1990) "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained $\text{Si}_{0.7}\text{Ge}_{0.3}$ Layer as an Etch Stop," Journal of the Electrical Society, Vol. 137, No. 10 (October 1990) pp. 3219-3223.	
<i>OK</i>	C149	Huang et al., (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", 2001 Symposium on VLSI Technology, Digest of Technical Papers, pp. 57-58	
	C150	International Search Report for International Application No. PCT/US99/07849, August 16, 1999, 5 pages.	
	C151	International Search Report for International Application No. PCT/US01/46322, January 22, 2003, 4 pages.	
	C152	International Search Report for International Application No. PCT/US03/18007, January 5, 2004, 6 pages.	
<i>OK</i>	C153	Langdo et al., (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" IEEE International SOI Conference, pages 211-212 (XP002263057)	
	C154	Notice of Grounds of Rejection for Japanese Patent Application Serial No. 2000-544004, August 20, 2002, 4 pages (Japanese translation attached).	
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	C158	Written Opinion for International Application No. PCT/US01/46322, January 22, 2003, 2 pages.	

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